

# **FAIRCHILD TVS Is Now Part of**



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Please note: The acquisition of this portfolio aligns with our strategy to expand in power semiconductor applications while strengthening our core circuit protection business. All of the Fairchild orderable part numbers will remain unchanged in order to maintain consistency with our customers.

For more information regarding this acquisition please refer to ON Semi / Fairchild TVS Acquisition Q&A

Version: A1806



# R

# SMBJ5V0(C)A - SMBJ170(C)A 600 Watt Transient Voltage Suppressors

#### **Features**

- · Glass-Passivated Junction
- 600 W Peak Pulse Power Capability on 10/1000 μs Waveform.
- · Excellent Clamping Capability
- · Low-Incremental Surge Resistance
- Fast Response Time: Typically Less than 1.0 ps from 0 V to BV minimum for Unidirectional and 5.0 ns for Bidirectional
- Typical I<sub>R</sub> Less than 1.0 μA Above 10 V
- UL Certificate #E258596



#### SMB/DO-214AA

Band denotes cathode on unidirectional devices only. No band on bi-directional devices. Bi-directional types have CA suffix where electrical characteristics apply in both directions suitable for bi-directional applications.

# **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^{\circ}\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
P <sub>PPM</sub>	Peak Pulse Power Dissipation on 10/1000 μs Waveform	600	W
I <sub>PPM</sub>	Peak Pulse Current on 10/1000 μs Waveform	See Table	Α
I <sub>FSM</sub>	Non-Repetitive Peak Forward Surge Current Superimposed on Rated Load (JEDEC Method) <sup>(1)</sup>	100	А
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

#### Note:

1. Measured on 8.3 ms single half-sine wave or equivalent square wave: duty cycle = 4 pulses per minute maximum.

SMBJ5V0(C)A - SMBJ170(C)A

### **Electrical Characteristics**

Values are at  $T_A = 25$ °C unless otherwise noted.

Uni-Directional Bi-Directional (C) Device	Part Marking <sup>(2)</sup>	Reverse Stand-Off Voltage V <sub>RWM</sub> (V)	Vol	kdown tage R (V) Max.	Test Current I <sub>T</sub> (mA)	Clamping Voltage at I <sub>PPM</sub> V <sub>C</sub> (V)	Peak Pulse Current I <sub>PPM</sub> (A)	Reverse Leakage at V <sub>RWM</sub> I <sub>R</sub> (μΑ) <sup>(3)</sup>
SMBJ5V0(C)A	KE	5.0	6.40	7.00	10	9.2	65.2	800
SMBJ6V0(C)A	KG	6.0	6.67	7.37	10	10.3	58.3	800
SMBJ6V5(C)A	KK	6.5	7.22	7.98	10	11.2	53.6	500
SMBJ7V0(C)A	KM	7.0	7.78	8.60	10	12.0	50.0	200
SMBJ7V5(C)A	KP	7.5	8.33	9.21	1	12.9	46.5	100
SMBJ8V0(C)A	KR	8.0	8.89	9.83	1	13.6	44.1	50
SMBJ8V5(C)A	KT	8.5	9.44	10.4	1	14.4	41.7	20
SMBJ9V0(C)A	KV	9.0	10.0	11.1	1	15.4	39.0	10
SMBJ10(C)A	KX	10	11.1	12.8	1	17.0	35.3	5
SMBJ11(C)A	KZ	11	12.2	13.5	1	18.2	33.0	5
SMBJ12(C)A	LE	12	13.3	14.7	1	19.9	30.2	5
SMBJ13(C)A	LG	13	14.4	15.9	1	21.5	27.9	5
SMBJ14(C)A	LK	14	15.6	17.2	1	23.2	25.9	5
SMBJ15(C)A	LM	15	16.7	18.5	1	24.4	24.6	5
SMBJ16(C)A	LP	16	17.8	19.7	1	26.0	23.1	5
SMBJ17(C)A	LR	17	18.9	20.9	1	27.6	21.7	5
SMBJ18(C)A	LT	18	20.0	22.1	1	29.2	20.5	5
SMBJ20(C)A	LV	20	22.2	24.5	1	32.4	18.5	5
SMBJ22(C)A	LX	22	24.4	26.9	1	35.5	16.9	5
SMBJ24(C)A	LZ	24	26.7	29.5	1	38.9	15.4	5
SMBJ26(C)A	ME	26	28.9	31.9	1	42.1	14.3	5
SMBJ28(C)A	MG	28	31.1	34.4	1	45.4	13.2	5
SMBJ30(C)A	MK	30	33.3	36.8	1	48.4	12.4	5
SMBJ33(C)A	MM	33	36.7	40.6	1	53.3	11.3	5
SMBJ36(C)A	MP	36	40.0	44.2	1	58.1	10.3	5
SMBJ40(C)A	MR	40	44.4	49.1	1	64.5	9.3	5
SMBJ43(C)A	MT	43	47.8	52.8	1	69.4	8.6	5
SMBJ45(C)A	MV	45	50.0	55.3	1	72.7	8.3	5
SMBJ48(C)A	MX	48	53.3	58.9	1	77.4	7.8	5
SMBJ51(C)A	MZ	51	56.7	62.7	1	82.4	7.3	5
SMBJ54(C)A	NE NE	54	60.0	66.3	1	87.1	6.9	5
SMBJ58(C)A	NG	58	64.4	71.2	1	93.6	6.4	5
SMBJ60(C)A	NK	60	66.7	73.7	1	96.8	6.2	5
SMBJ64(C)A	NM	64	71.1	78.6	1	103.0	5.8	5
SMBJ70(C)A	NP	70	77.8	86.0	1	113.0	5.3	5
SMBJ75(C)A	NR	75	83.3	92.1	1	121.0	5.0	5
SMBJ78(C)A	NT	75 78			1		4.8	5
SIVIDJ/8(C)A	IN I	78	86.7	95.8	l I	126.0	4.8	၁

#### Notes:

- 2. Color band denotes cathode on unidirectional devices only. No color band on bidirectional devices.
- 3. For bidirectional parts with  $V_{RWM}$  < 10 V, the  $I_R$  max limit is doubled.

# **Electrical Characteristics** (Continued)

Values are at  $T_A$  = 25°C unless otherwise noted.

Uni-Directional Bi-Directional (C) Device	Part Marking <sup>(2)</sup>	Reverse Stand-Off Voltage	Volt	down age (V)	Test Current	Clamping Voltage at I <sub>PPM</sub>	Peak Pulse Current	Reverse Leakage at V <sub>RWM</sub>
Device		V <sub>RWM</sub> (V)	Min.	Max.	I <sub>T</sub> (mA)	V <sub>C</sub> (V)	I <sub>PPM</sub> (A)	I <sub>R</sub> (μΑ) <sup>(3)</sup>
SMBJ85(C)A	NV	85	94.4	104.0	1	137.0	4.4	5
SMBJ90(C)A	NX	90	100.0	111.0	1	146.0	4.1	5
SMBJ100(C)A	NZ	100	111.0	123.0	1	162.0	3.7	5
SMBJ110(C)A	PE	110	122.0	135.0	1	177.0	3.4	5
SMBJ120(C)A	PG	120	133.0	147.0	1	193.0	3.1	5
SMBJ130(C)A	PK	130	144.0	159.0	1	209.0	2.9	5
SMBJ150(C)A	PM	150	167.0	185.0	1	243.0	2.5	5
SMBJ160(C)A	PP	160	178.0	197.0	1	259.0	2.3	5
SMBJ170(C)A	PR	170	189.0	209.0	1	275.0	2.2	5

#### Notes:

- 2. Color band denotes cathode on unidirectional devices only. No color band on bidirectional devices.
- 3. For bidirectional parts with  $\rm V_{RWM}$  < 10 V, the  $\rm I_{R}$  max limit is doubled.

# **Typical Performance Characteristics**

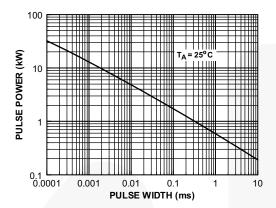


Figure 1. Peak Pulse Power Rating Curve

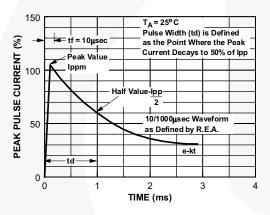


Figure 3. Pulse Waveform

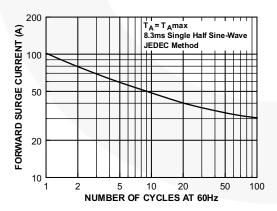


Figure 5. Non-Repetitive Surge Current

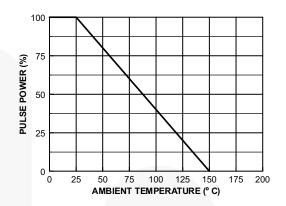


Figure 2. Pulse Derating Curve

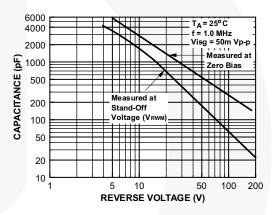
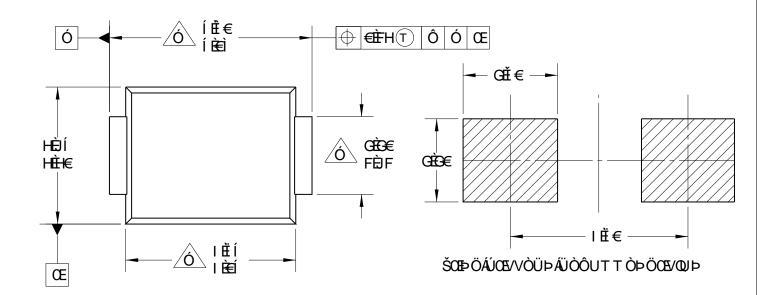
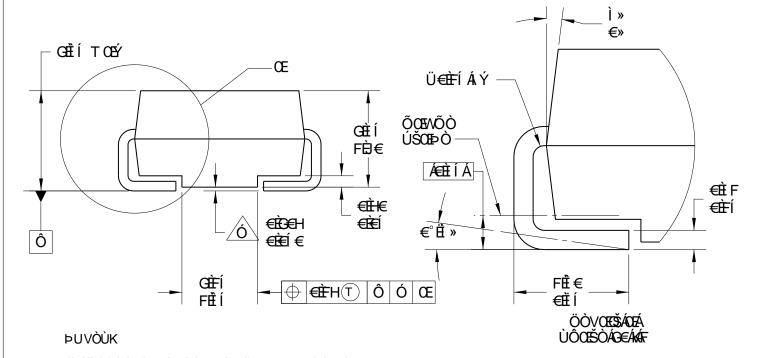


Figure 4. Junction Capacitance

Ú¢WWXÓÜ					
ÞÓÜ ÖÖÙÔÜŴVØÞ		ÖŒ/Ò	ÓŸÐÐÐÚŰÖ		
F	ÜÒŠÒŒÙÒÖÁ/U <i>Ä</i> ÖÔÔ	FJT ŒŸŒ€ÈÌ	ÙÖŠÒÒÆÓÐÙÙZ		





ÁŒÒÝÔÒÚVÁ PÒÜÒÁPUVÒÖÁÔUÞØUÜT ÙÁVUÁ

RÒÖÒÔÁÖU GFI ÁK GEÜ GOEV QU ÞÁQEÐE Ó ÖU ÒÙÁÞU VÁÔU T Ú ŠÝ ÁRÒÖÔÔÁÙ VÖ EÁK GĚ WÒÈ ÁKÔ EÁGES ÁÖGT ÒÞÙ QU ÞÙ AGEÜ ÒÁÐA ÁT GŠŠGT ÒV ÒÜ Ù È ÁKÔ EÁÖGT ÒÞÙ QU ÞÙ ÁGEÐ ÁOÝ Ô ŠVÝ ÚG KÔÁU ÁÁOWÜ Ü Ù Ê

ÁT U ŠÖÁØŠŒÙ PÁŒP ÖÁV®ÁÓŒÜÁÚÜU VÜWÙ@JÞÙÈ ÁKÒ PÁÖCT, Ò Þ Ù QU ÞÁCTÞ ÖÁ / U Š Ò Ü CTÞ Ô ÒÁCTÙ ÁÚ Ò Ü ÁCTÙ T ÒÁKKÁ ŸFIĚĖJJIÈ

ÁKØÈÁŠOEÞÖÁÚOE√VÒÜÞÁÙVÖÈÆÖQUTÍHHÎÝGI€TÈ ÁNŐ ÉKÖÜCEY OÞŐÁZOŠÓÁÞOET ÓKKÖUGFI OEDEÜÓXF

	ŒÚÚÜUXŒŠÙ	ÖV <b>Z</b> OÖ					
	<sup>ŎŨŒY ÞK</sup> ÓUÓUŸÁTŒŠÖU	FJT ŒŸŒ€ÈÌ		AIR	CHILE		
	<sup>ÓPÓÓSÒÖK</sup> ÙÖÆSÒÒ		SEMICONDUCTOR TM				
	œúûuxòŏk ØÜÒÖÁÜÒÞ		GŠÖÉÁÚT ÓÉÁRÒÖÒÔ				
	ŒŰŰUXĊŎK PUYŒŰÖÁŒŠŠÒÞ		ÖUGFIÁXŒÜQŒVQUÞÁŒŒ				Ξ
	ÚÚURÓÓVQIÞ ŽTTÁ OÓP		FKF ÞEÐE TSVEÖUGFIGÐE		üàx F		
			ØUÜT ÒÜŠŸK ÞÆŒ		ÚPÔÔVÁK FÁUØÁF		